

IN THE CLAIMS

1. (currently amended) A multi-layered structure for fabricating an ohmic electrode, comprising a non-single crystal semiconductor layer comprising In and a film including at least a metal nitride film which are sequentially stacked on a III-V compound semiconductor body, wherein said metal nitride film is selected from the group consisting of a WSiN film, a TaN film, a TaSiN film, and a TiSiN film, and a TiON film.
2. (previously presented) The multi-layered structure for fabricating an ohmic electrode according to claim 1 wherein said III-V compound semiconductor body comprises GaAs, AlGaAs or InGaAs.
3. (previously presented) The multi-layered structure for fabricating an ohmic electrode according to claim 1 wherein said non-single crystal semiconductor layer is a non-single crystal  $\text{In}_x\text{Ga}_{1-x}\text{As}$  ( $0 < x \leq 1$ ) layer.
4. (previously presented) The multi-layered structure for fabricating an ohmic electrode according to claim 1 wherein said film comprises a metal film and wherein the metal nitride film is formed on said metal film.
5. (previously presented) The multi-layered structure for fabricating an ohmic electrode according to claim 4 wherein a refractory metal film is further provided on said metal nitride film.
6. (previously presented) The multi-layered structure for fabricating an ohmic electrode according to claim 5 wherein a further metal film for wiring is further provided on said refractory metal film.
7. (previously presented) The multi-layered structure for fabricating an ohmic electrode according to claim 4 wherein said metal film is one of a Ni film, a Co film, and an Al film.
8. (previously presented) The multi-layered structure for fabricating an ohmic electrode according to claim 5 wherein said refractory metal film is a W film, a Ta film or a Mo film.

9. (currently amended) A multi-layered structure for fabricating an ohmic electrode, comprising a non-single crystal semiconductor layer comprising In and a film including at least a metal nitride film which are sequentially stacked on a III-V compound semiconductor body,

the energy barrier between said non-single crystal semiconductor layer and said film being lower than the energy barrier between said III-V compound semiconductor body and said film, wherein said metal nitride film is selected from the group consisting of a WSiN film, a TaN film, a TaSiN film, and a TiSiN film, and a TiON film.

10. (currently amended) An ohmic electrode obtained by annealing a multi-layered structure for fabricating an ohmic electrode, comprising a non-single crystal semiconductor layer comprising In and a film including at least a metal nitride film which are sequentially stacked on a III-V compound semiconductor body, wherein said metal nitride film is selected from the group consisting of a WSiN film, a TaN film, a TaSiN film, and a TiSiN film, and a TiON film.

11. (previously presented) The ohmic electrode according to claim 10 wherein the annealing temperature of said multi-layered structure for fabricating an ohmic electrode is 500°C to 600°C.

12. (previously presented) The ohmic electrode according to claim 10 obtained by annealing said multi-layered structure for fabricating an ohmic electrode in which said III-V compound semiconductor body comprises GaAs, AlGaAs or InGaAs.

13. (previously presented) The ohmic electrode according to claim 10 obtained by annealing said multi-layered structure for fabricating an ohmic electrode in which said non-single crystal semiconductor layer is a non-single crystal  $In_xGa_{1-x}As$  ( $0 < x \leq 1$ ) layer).

14. (previously presented) The ohmic electrode according to claim 10 obtained by annealing said multi-layered structure for fabricating an ohmic electrode in which said film comprises a metal film and wherein the metal nitride film is provided on said metal film.

15. (previously presented) The ohmic electrode according to claim 10 obtained by annealing said multi-layered structure for fabricating an ohmic electrode in which a refractory metal film is further provided on said metal nitride film.

16. (previously presented) The ohmic electrode according to claim 15 obtained by annealing said multi-layered structure for fabricating an ohmic electrode in which a further metal film for wiring is provided on said refractory metal film.

17. (previously presented) The ohmic electrode according to claim 14 obtained by annealing said multi-layered structure for fabricating an ohmic electrode in which said metal film is one of a Ni film, a Co film, and an Al film.

18. (previously presented) The ohmic electrode according to claim 15 obtained by annealing said multi-layered structure for fabricating an ohmic electrode in which said refractory metal film is a W film, a Ta film or a Mo film.

19. (currently amended) An ohmic electrode provided on a III-V compound semiconductor body obtained by annealing a multi-layered structure for fabricating an ohmic electrode, comprising a non-single crystal semiconductor layer comprised of In and a film including at least a metal nitride film,

the energy barrier between said non-single crystal semiconductor layer and said film being lower than the energy barrier between said III-V compound semiconductor body and said film, wherein said metal nitride film is selected from the group consisting of a WSiN film, a TaN film, a TaSiN film, and a TiSiN film, ~~and~~ ~~a~~ ~~TiON film~~.